Supplementary Information

for

Control of magnetization-reversal processes via uniaxial anisotropy strength in $La_{0.67}Sr_{0.33}MnO_3$ electrodes for spintronic devices

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Supplementary Note 1

XRD data on LSMO films on NGO substrates

All LSMO films present strong Laue fringes in x-ray diffraction, and are thus coherently strained through their thickness.

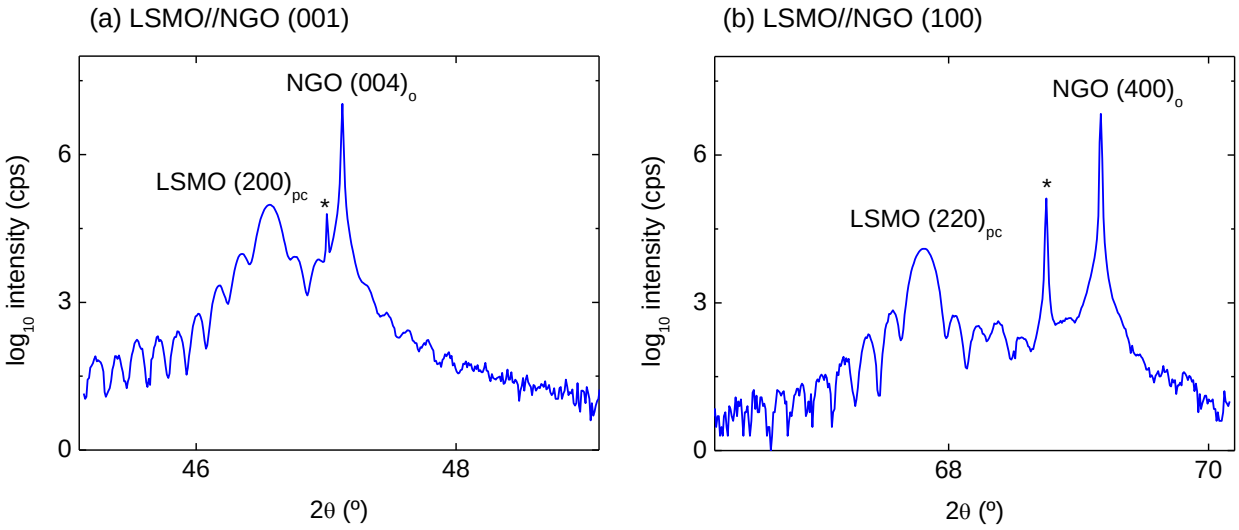

Fig. S1. High-resolution x-ray diffraction data: out-of-plane ω-2θ scans of (a) a 60 nm-thick LSMO film grown on $NdGaO_3$ (001); (b) a 61 nm-thick LSMO film grown on $NdGaO_3$ (100). Subscripts denote orthorhombic (o) and pseudocubic (pc) crystal systems. Asterisks (*) denote substrate twins.